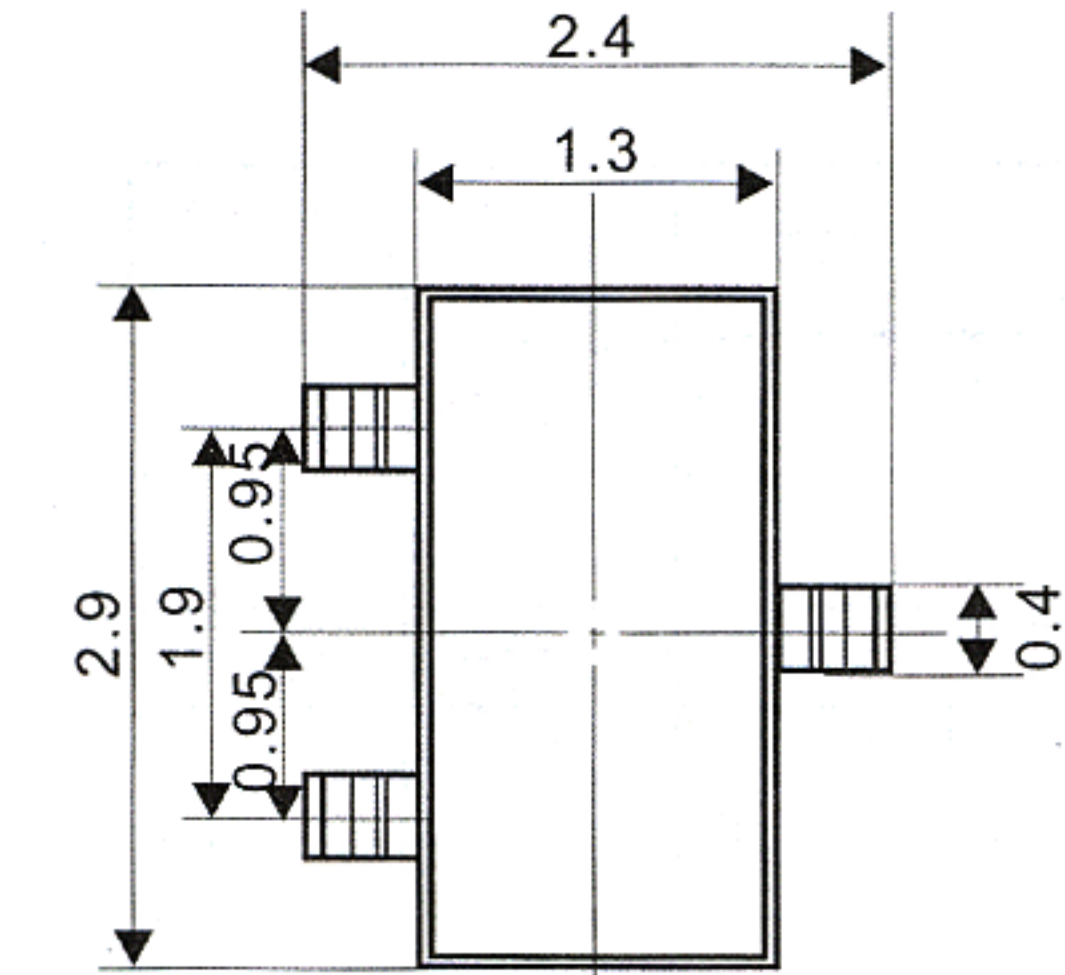
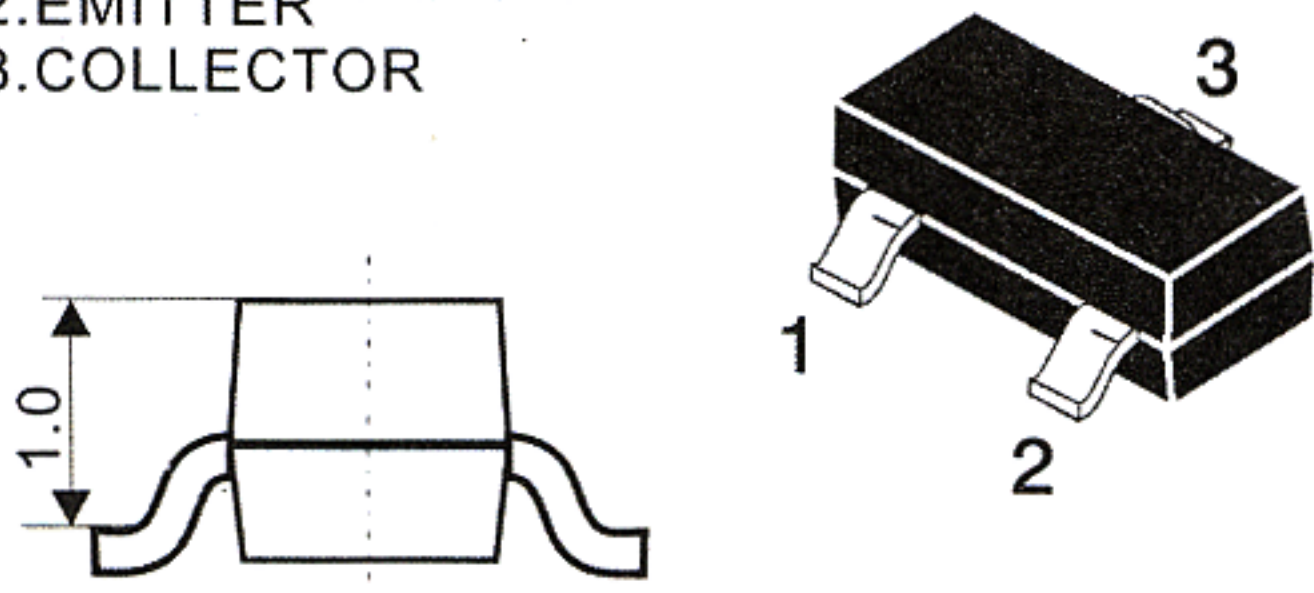


SOT-23 Plastic-Encapsulate Transistors

S9015LT1 TRANSISTOR (PNP)

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



UNIT: mm

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -50V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

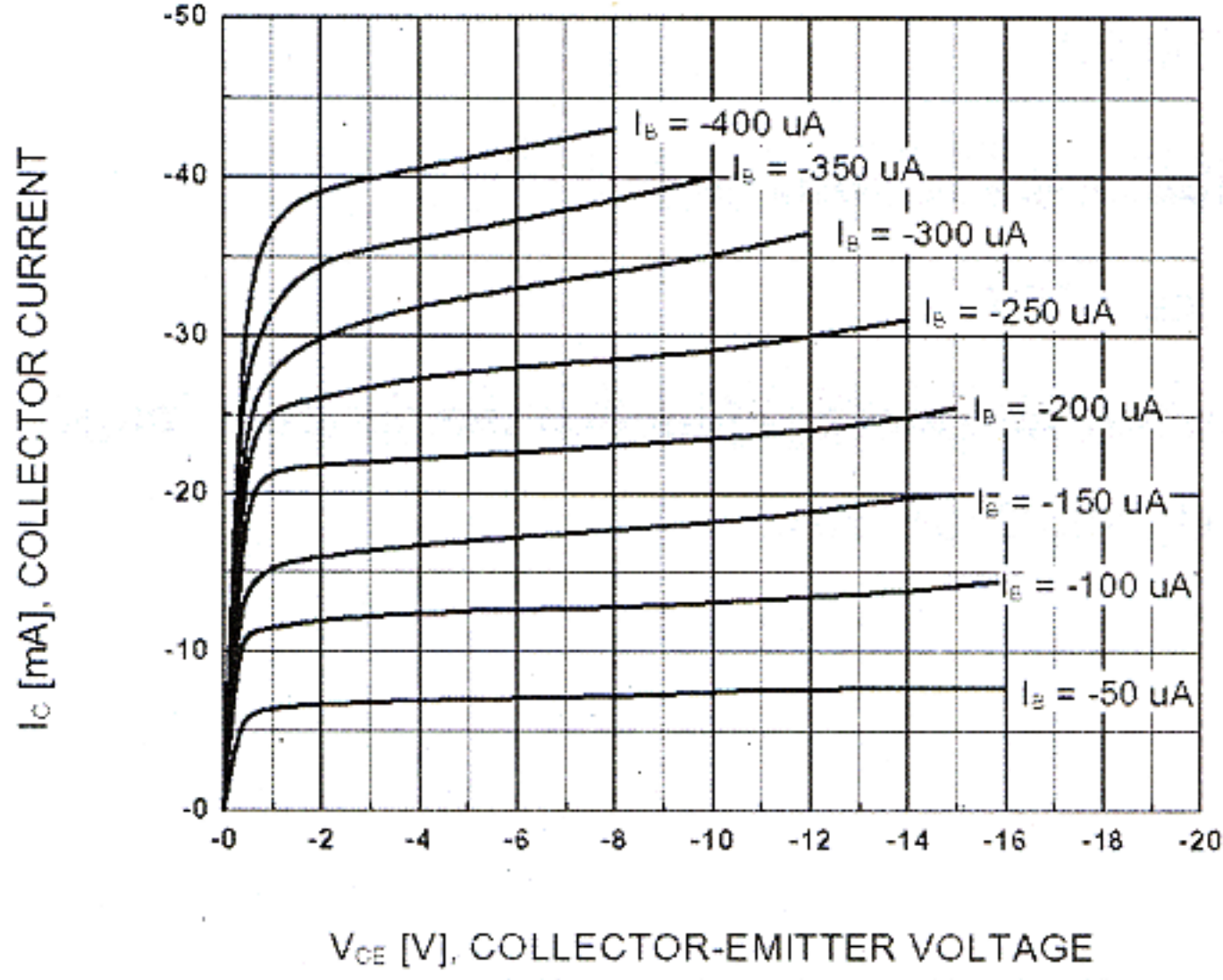
($T_{amp}=25^{\circ}C$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|--------------------------------------|---------------|--------------------------------------|-----|-----|-------|---------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=-100\mu A, I_E=0$ | -50 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=-1mA, I_B=0$ | -45 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=-100\mu A, I_C=0$ | -5 | | -0.05 | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=-50V, I_E=0$ | | | -0.05 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=-5V, I_C=0$ | | | 1000 | μA |
| DC current gain | h_{FE} | $V_{CE}=-5V, I_C=-1mA$ | 200 | | -0.3 | |
| Collector-emitter saturation voltage | V_{CEsat} | $I_C=-100mA, I_B=-10mA$ | | | -1 | V |
| Base-emitter saturation voltage | V_{BEsat} | $I_C=-100mA, I_B=-10mA$ | | | | V |
| Transition frequency | f_T | $V_{CE}=-5V, I_C=-10mA$ $f=30MHz$ | 150 | | | MHz |

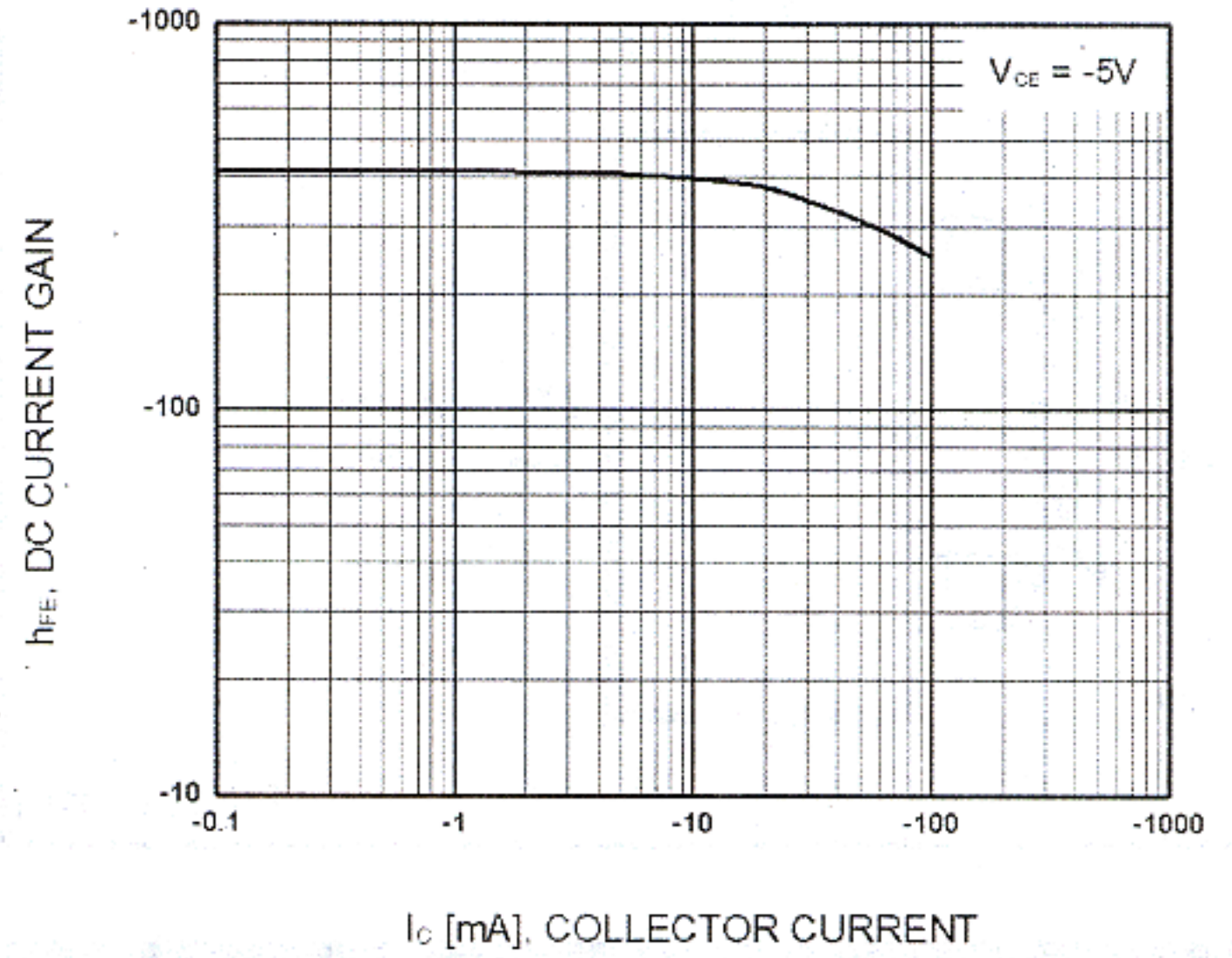
CLASSIFICATION OF h_{FE}

| Rank | L | H |
|-------|---------|----------|
| Range | 200-450 | 450-1000 |

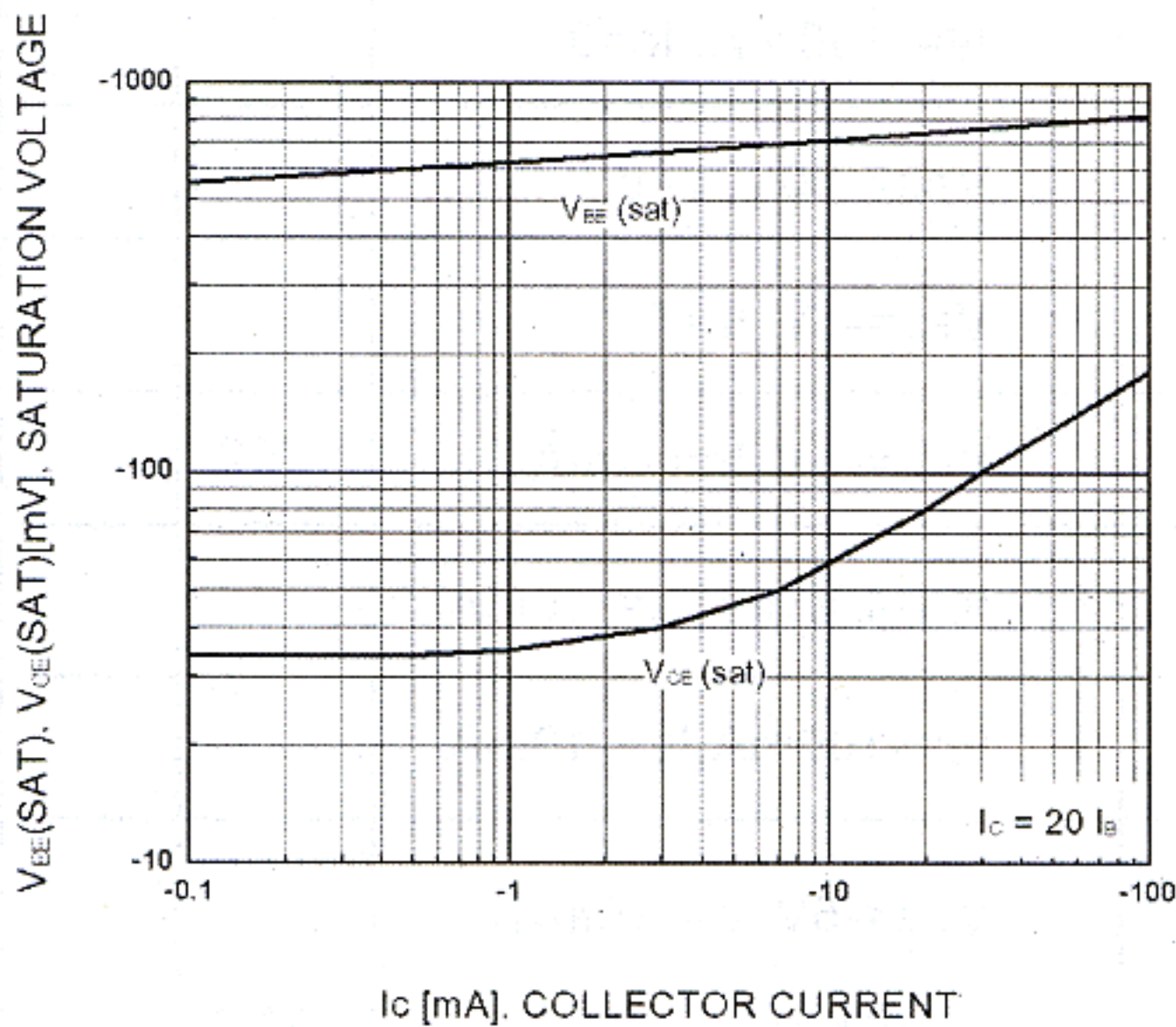
DEVICE MARKING : S9015LT1=M6



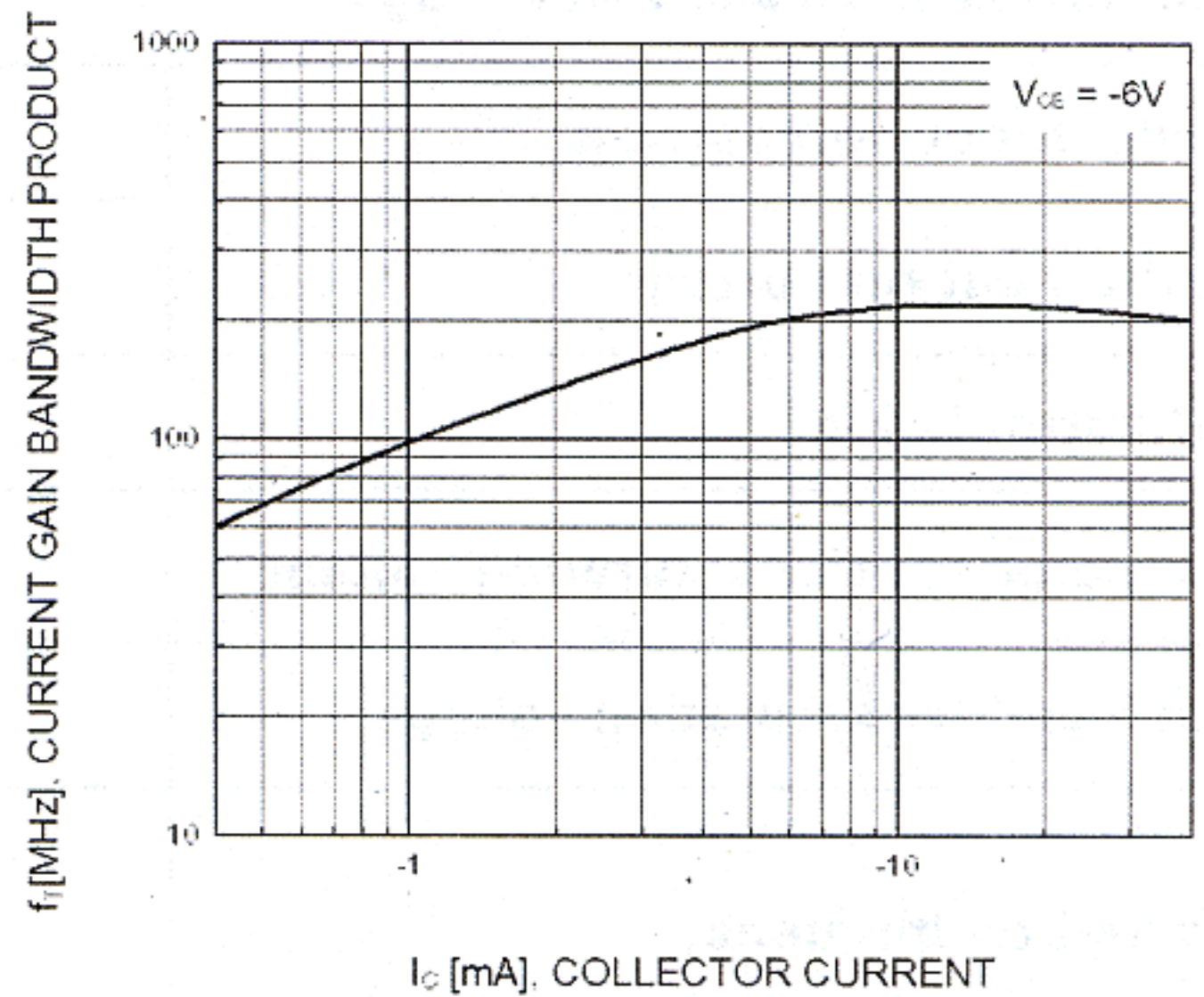
Static Characteristic



DC Current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product